**Product data sheet** 

## 1. General description

NPN/NPN matched double transistor in a very small SOT363 (TSSOP6) Surface-Mounted Device (SMD) plastic package. The transistors are fully isolated internally.

# 2. Features and benefits

- Current gain matching
- Base-emitter voltage matching
- Drop-in replacement for standard double transistors
- AEC-Q101 qualified

## 3. Applications

- Current mirror
- · Differential amplifier

## 4. Quick reference data

Table 1. Quick reference data

| Symbol                             | Parameter                 | Conditions  |     | Min | Тур | Max | Unit |  |  |
|------------------------------------|---------------------------|---|-----|-----|-----|-----|------|--|--|
| Per transistor                     | Per transistor            |   |     |     |     |     |      |  |  |
| V <sub>CEO</sub>                   | collector-emitter voltage | open base   |     | -   | -   | 65  | V    |  |  |
| I <sub>C</sub>                     | collector current         |   |     | -   | -   | 100 | mA   |  |  |
| Per transistor                     |                           |   |     |     |     |     |      |  |  |
| h <sub>FE</sub>                    | DC current gain           | $V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$ |     | 200 | 290 | 450 |      |  |  |
| Per device                         | Per device                |   |     |     |     |     |      |  |  |
| h <sub>FE1</sub> /h <sub>FE2</sub> | h <sub>FE</sub> matching  | $V_{CE} = 5 \text{ V; } I_{C} = 2 \text{ mA; } T_{amb} = 25 \text{ °C}$     | [1] | 0.9 | 1   | -   |      |  |  |
| V <sub>BE1</sub> -V <sub>BE2</sub> | V <sub>BE</sub> matching  |   | [2] | -   | -   | 2   | mV   |  |  |

- [1] The smaller of the two values is taken as numerator.
- [2] The smaller of the two values is subtracted from the larger value.





### **NPN/NPN** matched double transistor

# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description   | Simplified outline | Graphic symbol |
|-----|--------|---------------|--------------------|----------------|
| 1   | Е      | emitter TR1   | 654                | 6 5 4          |
| 2   | В      | base TR1      |                    | 1770           |
| 3   | С      | collector TR2 | 0                  | TR1 TR2        |
| 4   | E      | emitter TR2   | ☐1 ☐2 ☐3           |                |
| 5   | В      | base TR2      | TSSOP6 (SOT363)    | 1 2 3          |
| 6   | С      | collector TR1 |                    | sym020         |

# 6. Ordering information

Table 3. Ordering information

| Type number |          | Package |  |         |  |  |  |
|-------------|----------|---------|--|---------|--|--|--|
|             |          | Name    | Description                              | Version |  |  |  |
|             | BCM846BS | TSSOP6  | plastic surface-mounted package; 6 leads | SOT363  |  |  |  |

# 7. Marking

Table 4. Marking codes

| Type number | Marking code [1] |
|-------------|------------------|
| BCM846BS    | F2%              |

[1] % = placeholder for manufacturing site code

#### **NPN/NPN** matched double transistor

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                          |     | Min | Max | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|-----|------|
| Per transis      | tor                       |                                     | '   |     |     | _    |
| $V_{CBO}$        | collector-base voltage    | open emitter                        |     | -   | 80  | V    |
| $V_{CEO}$        | collector-emitter voltage | open base                           |     | -   | 65  | V    |
| $V_{EBO}$        | emitter-base voltage      | open collector                      |     | -   | 6   | V    |
| I <sub>C</sub>   | collector current         |                                     |     | -   | 100 | mA   |
| I <sub>CM</sub>  | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | 200 | mA   |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 200 | mW   |
| Per device       |                           |                                     |     |     |     |      |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 300 | mW   |
| Tj               | junction temperature      |                                     |     | -   | 150 | °C   |
| T <sub>amb</sub> | ambient temperature       |                                     |     | -55 | 150 | °C   |
| T <sub>stg</sub> | storage temperature       |                                     |     | -65 | 150 | °C   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter   | Conditions  |     | Min | Тур | Max | Unit |  |
|----------------|---|-------------|-----|-----|-----|-----|------|--|
| Per transistor | Per transistor                                    |             |     |     |     |     |      |  |
| $R_{th(j-a)}$  | thermal resistance<br>from junction to<br>ambient | in free air | [1] | -   | -   | 625 | K/W  |  |
| Per device     |   |             |     |     |     |     |      |  |
| $R_{th(j-a)}$  | thermal resistance<br>from junction to<br>ambient | in free air | [1] | -   | -   | 416 | K/W  |  |

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

BCM846BS

### **NPN/NPN** matched double transistor

## 10. Characteristics

Table 7. Characteristics

| Symbol                             | Parameter                    | Conditions  |     | Min | Тур | Max | Unit |
|------------------------------------|------------------------------|---|-----|-----|-----|-----|------|
| Per transi                         | stor                         |   |     |     |     |     |      |
| I <sub>CBO</sub>                   | collector-base cut-off       | V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C  |     | -   | -   | 15  | nA   |
|                                    | current                      | V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C   |     | -   | -   | 5   | μΑ   |
| I <sub>EBO</sub>                   | emitter-base cut-off current | V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C   |     | -   | -   | 100 | nA   |
| h <sub>FE</sub>                    | DC current gain              | $V_{CE}$ = 5 V; $I_{C}$ = 2 mA; $T_{amb}$ = 25 °C   |     | 200 | 290 | 450 |      |
|                                    |                              | V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 μA; T <sub>amb</sub> = 25 °C   |     | -   | 250 | -   |      |
| V <sub>CEsat</sub>                 | collector-emitter            | $I_C$ = 10 mA; $I_B$ = 0.5 mA; $T_{amb}$ = 25 °C  |     | -   | 50  | 200 | mV   |
|                                    | saturation voltage           | $I_C$ = 100 mA; $I_B$ = 5 mA; pulsed;   |     | -   | 200 | 400 | mV   |
| V <sub>BEsat</sub>                 | base-emitter saturation      | $t_p \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C$  | [1] | -   | 910 | -   | mV   |
|                                    | voltage                      | $I_C$ = 10 mA; $I_B$ = 0.5 mA; $T_{amb}$ = 25 °C  | [1] | -   | 760 | -   | mV   |
| $V_{BE}$                           | base-emitter voltage         | $V_{CE}$ = 5 V; $I_{C}$ = 10 mA; $T_{amb}$ = 25 °C  | [2] | -   | -   | 770 | mV   |
| $V_{BE}$                           | base-emitter voltage         | $V_{CE}$ = 5 V; $I_{C}$ = 2 mA; $T_{amb}$ = 25 °C   | [2] | 610 | 660 | 710 | mV   |
| C <sub>C</sub>                     | collector capacitance        | V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A;<br>f = 1 MHz; T <sub>amb</sub> = 25 °C                |     | -   | -   | 1.5 | pF   |
| C <sub>E</sub>                     | emitter capacitance          | $V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$<br>$f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$ |     | -   | 11  | -   | pF   |
| f <sub>T</sub>                     | transition frequency         | $V_{CE}$ = 5 V; $I_{C}$ = 10 mA; f = 100 MHz;<br>$T_{amb}$ = 25 °C  |     | 100 | 250 | -   | MH   |
| NF                                 | noise figure                 | $V_{CE}$ = 5 V; $I_{C}$ = 0.2 mA; $R_{S}$ = 2 k $\Omega$ ;<br>f = 1 kHz; B = 200 Hz; $T_{amb}$ = 25 °C                    |     | -   | 3.3 | -   | dB   |
|                                    |                              | $V_{CE}$ = 5 V; $I_{C}$ = 0.2 mA; $R_{S}$ = 2 k $\Omega$ ;<br>$T_{amb}$ = 25 °C; f = 10 Hz to 15.7 kHz                    |     | -   | 2.8 | -   | dB   |
| Per device                         | <b>e</b>                     |   | 1   |     | 1   | 1   |      |
| h <sub>FE1</sub> /h <sub>FE2</sub> | h <sub>FE</sub> matching     | $V_{CE}$ = 5 V; $I_{C}$ = 2 mA; $T_{amb}$ = 25 °C   | [3] | 0.9 | 1   | -   |      |
| V <sub>BE1</sub> -V <sub>BE2</sub> | V <sub>BE</sub> matching     |   | [4] | -   | -   | 2   | mV   |

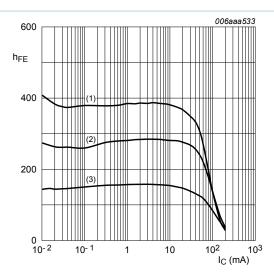
<sup>[1]</sup>  $V_{BEsat}$  decreases by about 1.7 mV/K with increasing temperature.

<sup>[2]</sup> V<sub>BE</sub> decreases by about 2 mV/K with increasing temperature.

<sup>[3]</sup> The smaller of the two values is taken as numerator.

<sup>[4]</sup> The smaller of the two values is subtracted from the larger value.

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$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 1. DC current gain as a function of collector current; typical values

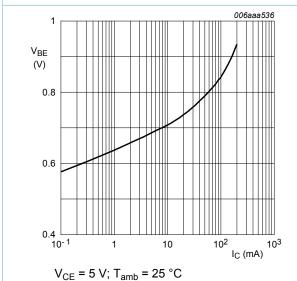


Fig. 3. Base-emitter voltage as a function of collector current; typical values

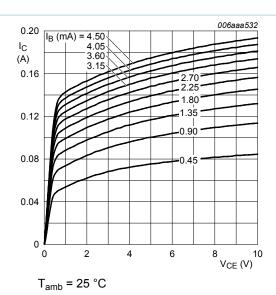
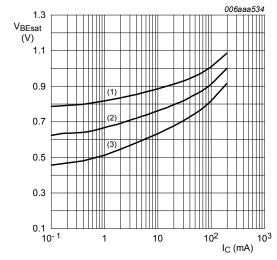


Fig. 2. Collector current as a function of collectoremitter voltage; typical values



 $I_{\rm C}/I_{\rm B} = 20$ 

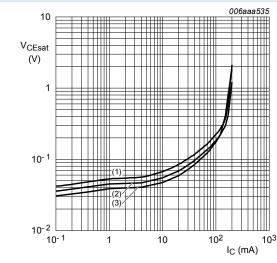
(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 4. Base-emitter saturation voltage as a function of collector current; typical values

### NPN/NPN matched double transistor



$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 5. Collector-emitter saturation voltage as a function of collector current; typical values

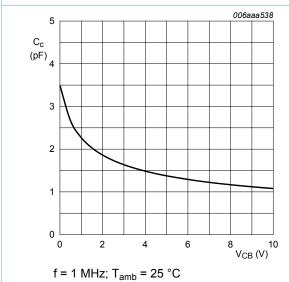
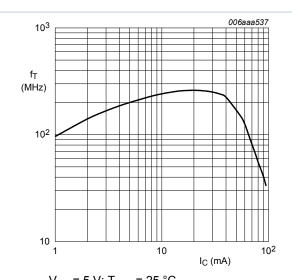
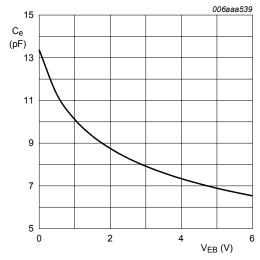


Fig. 7. Collector capacitance as a function of collectorbase voltage; typical values



 $V_{CE}$  = 5 V;  $T_{amb}$  = 25 °C

Fig. 6. Transition frequency as a function of collector current; typical values



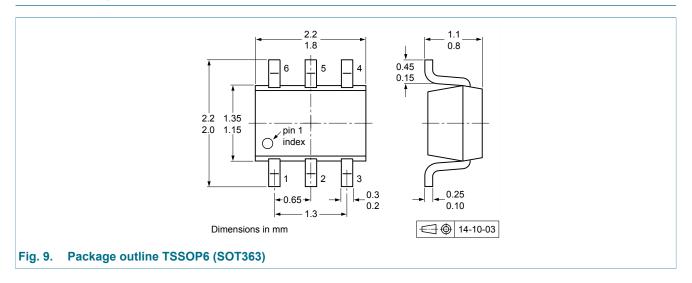
f = 1 MHz; T<sub>amb</sub> = 25 °C

Emitter capacitance as a function of emitterbase voltage; typical values

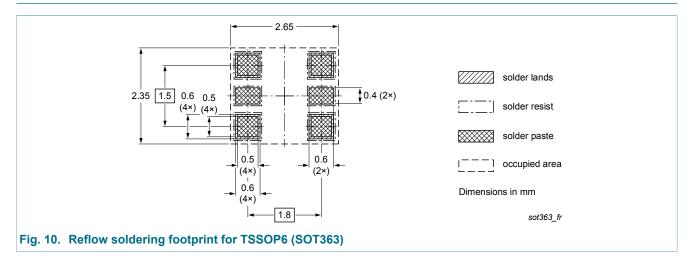
6/12

#### NPN/NPN matched double transistor

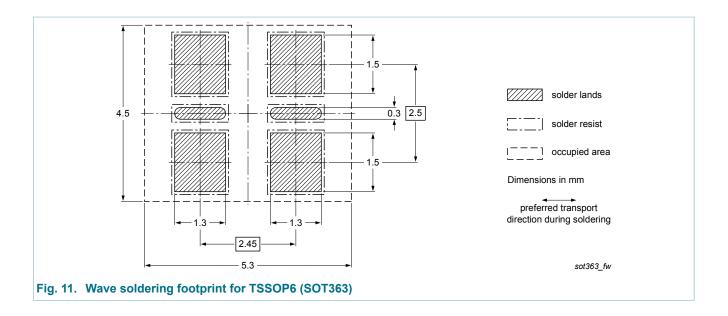
# 11. Package outline



# 12. Soldering



### **NPN/NPN** matched double transistor



### **NPN/NPN** matched double transistor

# 13. Revision history

### Table 8. Revision history

| Data sheet ID | Release date           | Data sheet status    | Change notice | Supersedes   |  |
|---------------|------------------------|----------------------|---------------|--------------|--|
| BCM846BS v.2  | 20150626               | Product data sheet   | -             | BCM846BS v.1 |  |
| Modification: | Product status changed |                      |               |              |  |
| BCM846BS v.1  | 20150424               | Objective data sheet | -             | -            |  |

#### NPN/NPN matched double transistor

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|--------------------------------------|--------------------|---|
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